

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	0.52	0.8	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ³⁾		-	-	40	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 125 \mu A$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS}=55V, V_{GS}=0V, T_j=25^{\circ}C$ $V_{DS}=55V, V_{GS}=0V, T_j=125^{\circ}C$	I_{DSS}	- -	0.01 1	1 100	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	1	100	
Drain-source on-state resistance $V_{GS}=10V, I_D=50A$	$R_{DS(on)}$	-	7.6	9.1	$m\Omega$

¹Current limited by bondwire ; with an $R_{thJC} = 0.8K/W$ the chip is able to carry $I_D = 99A$ at 25°C , for detailed information see app.-note ANPS071E available at www.infineon.com/optimos

²Defined by design. Not subject to production test.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 70A$	34	68	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	2360	3140	pF
Output capacitance	C_{oss}		-	610	810	
Reverse transfer capacitance	C_{rss}		-	150	230	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V$, $V_{GS} = 10V$, $I_D = 80A$, $R_G = 4.7\Omega$	-	14	21	ns
Rise time	t_r		-	29	44	
Turn-off delay time	$t_{d(off)}$		-	39	58	
Fall time	t_f		-	28	42	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 44V$, $I_D = 80A$	-	12	16	nC
Gate to drain charge	Q_{gd}		-	24	37	
Gate charge total	Q_g	$V_{DD} = 44V$, $I_D = 80A$, $V_{GS} = 0$ to $10V$	-	60	80	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 44V$, $I_D = 80A$	-	5.8	-	V

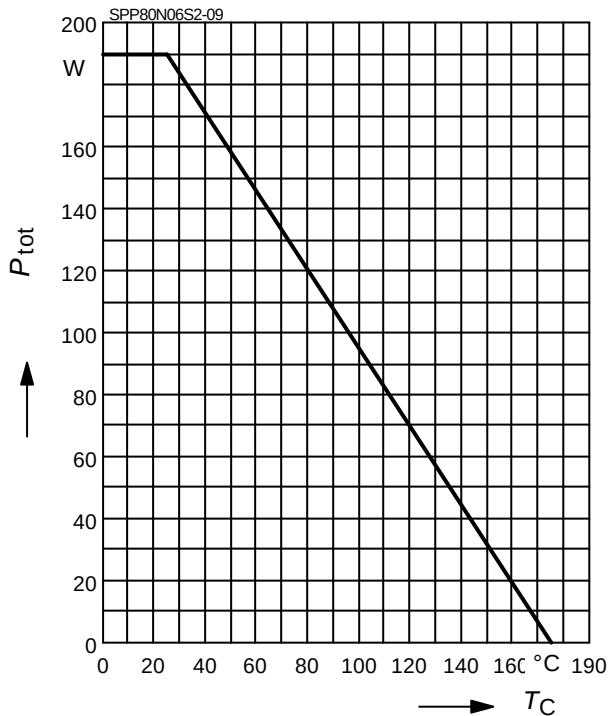
Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ C$	-	-	80	A
Inv. diode direct current, pulsed	I_{SM}		-	-	320	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V$, $I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	t_{rr}	$V_R = 30V$, $I_F = I_S$, $di_F/dt = 100A/\mu s$	-	50	63	ns
Reverse recovery charge	Q_{rr}		-	76	95	nC

1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

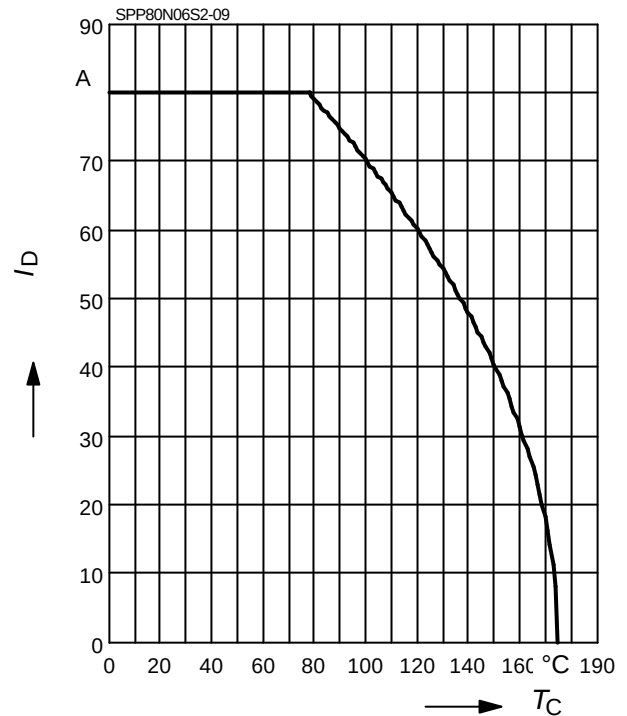
parameter: $V_{GS} \geq 6 \text{ V}$



2 Drain current

$$I_D = f(T_C)$$

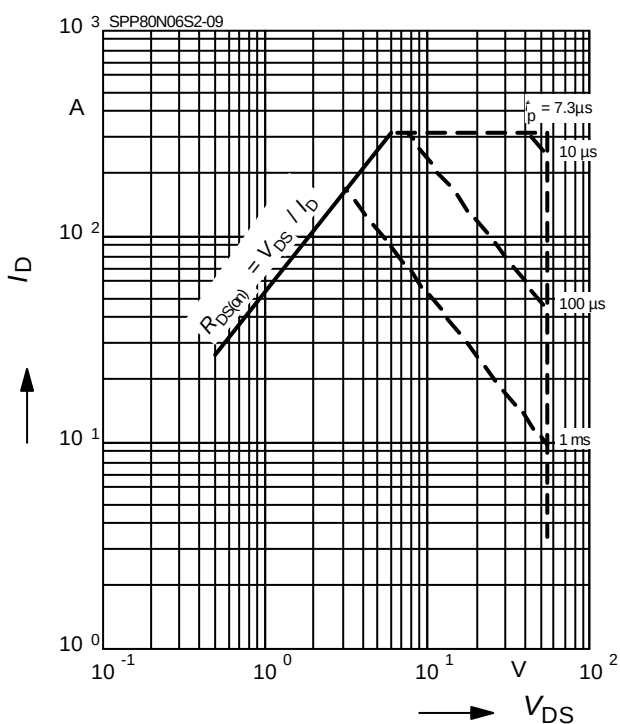
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

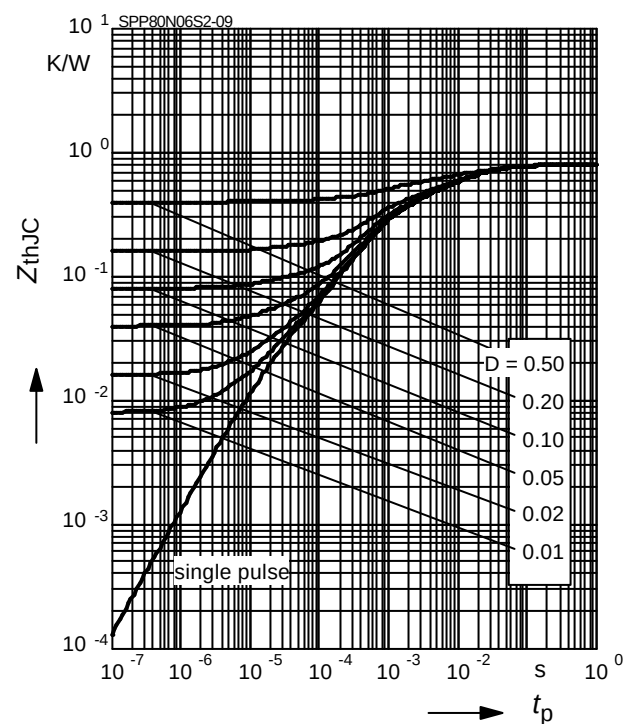
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

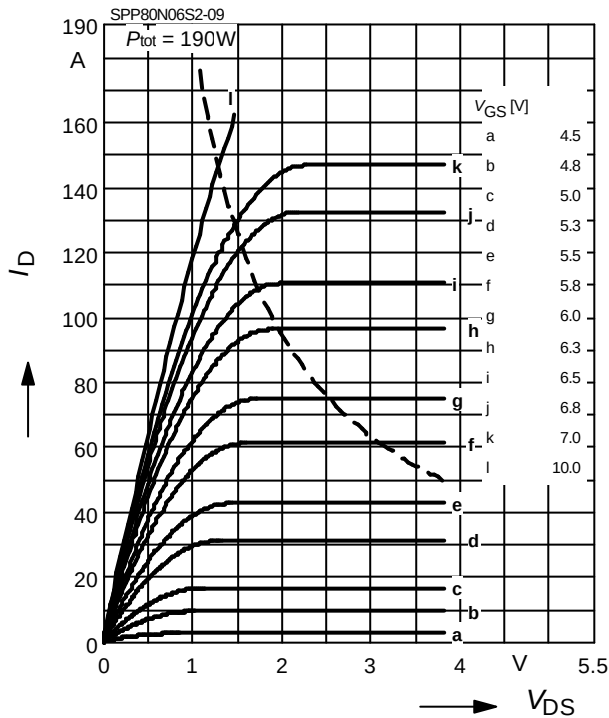
parameter: $D = t_p/T$



5 Typ. output characteristic

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

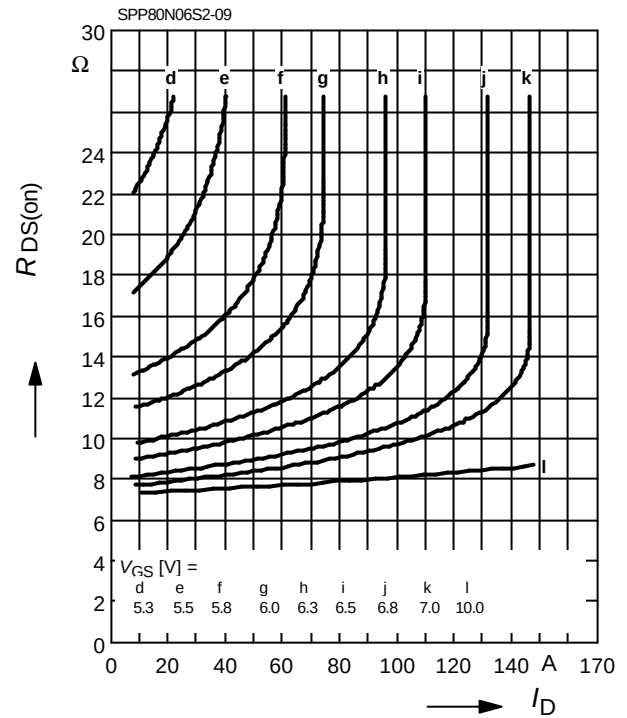
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

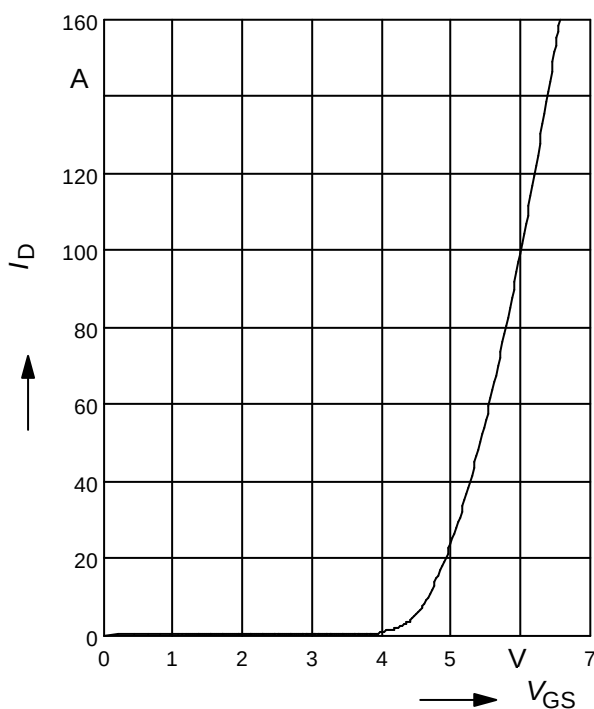
parameter: V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

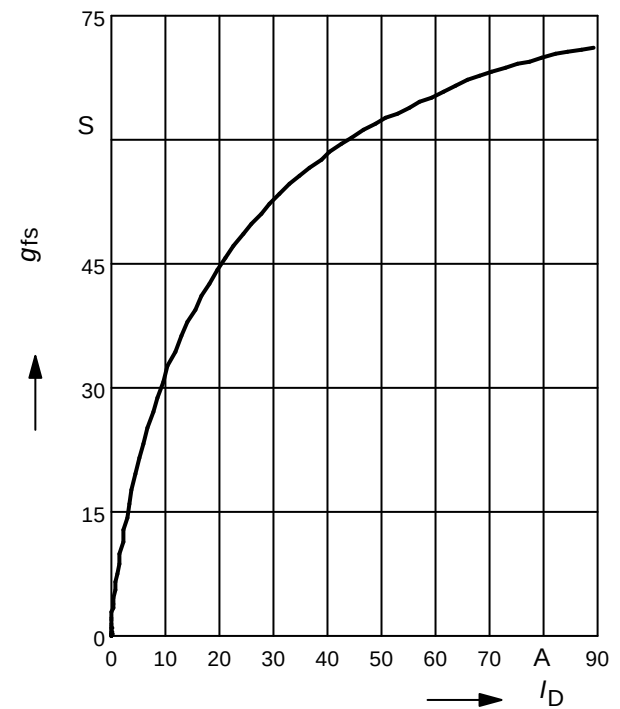
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$

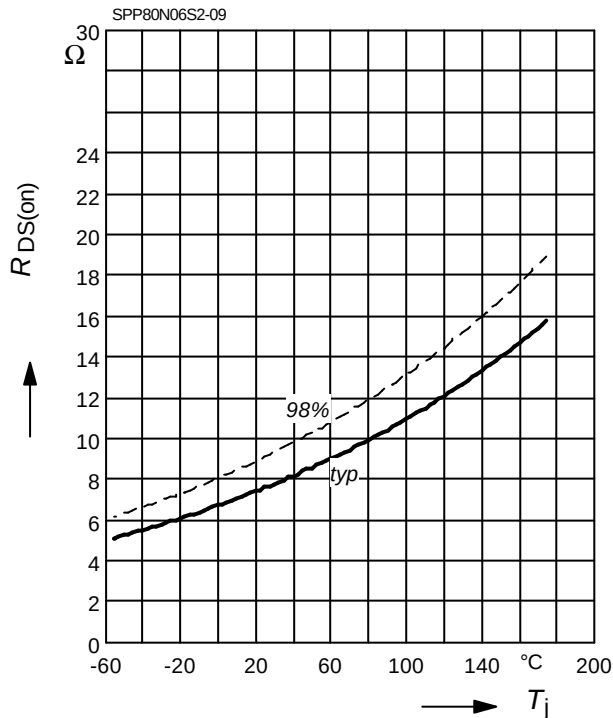
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

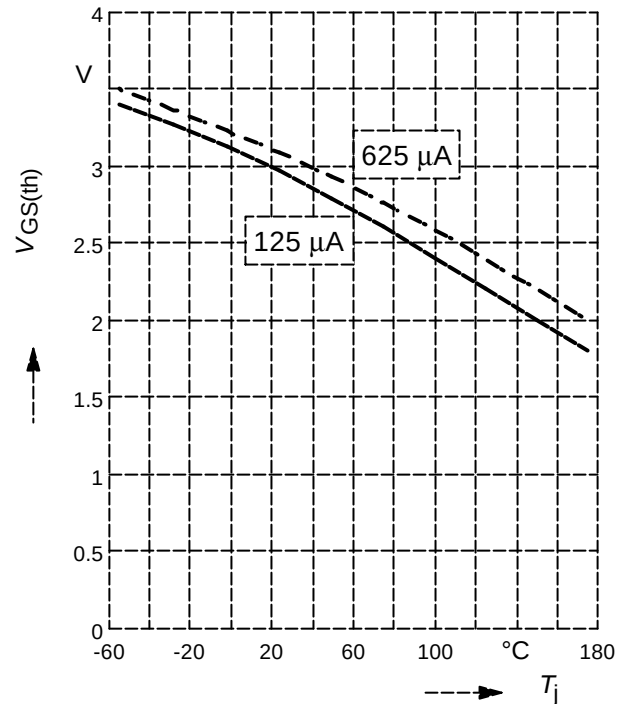
parameter: $I_D = 50\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

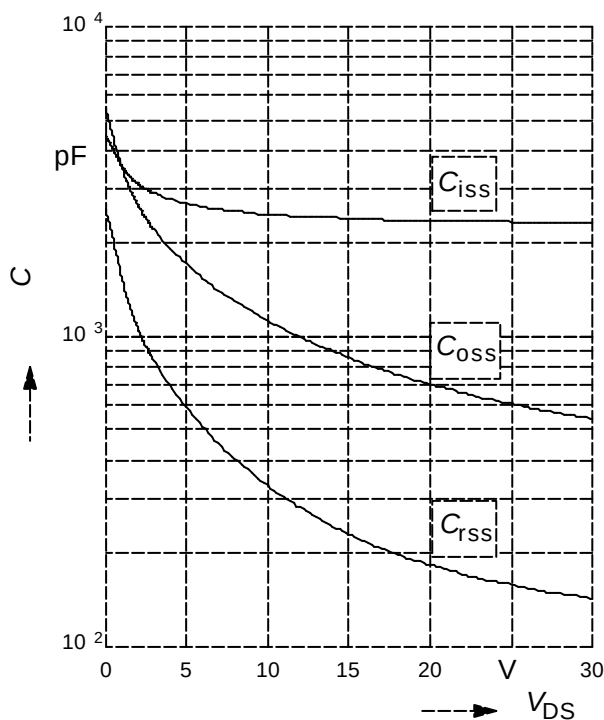
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

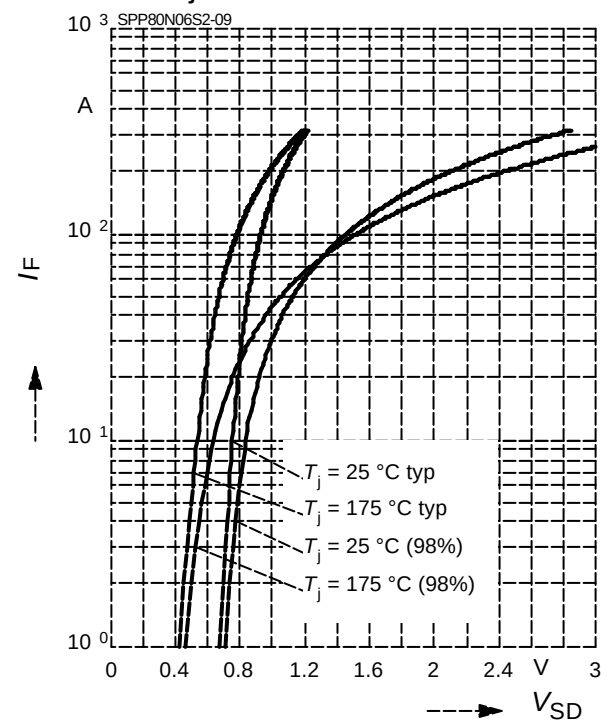
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

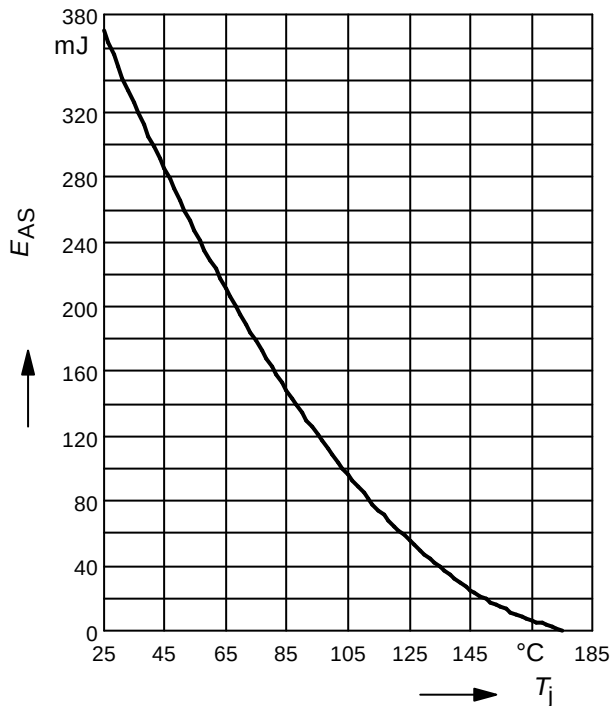
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

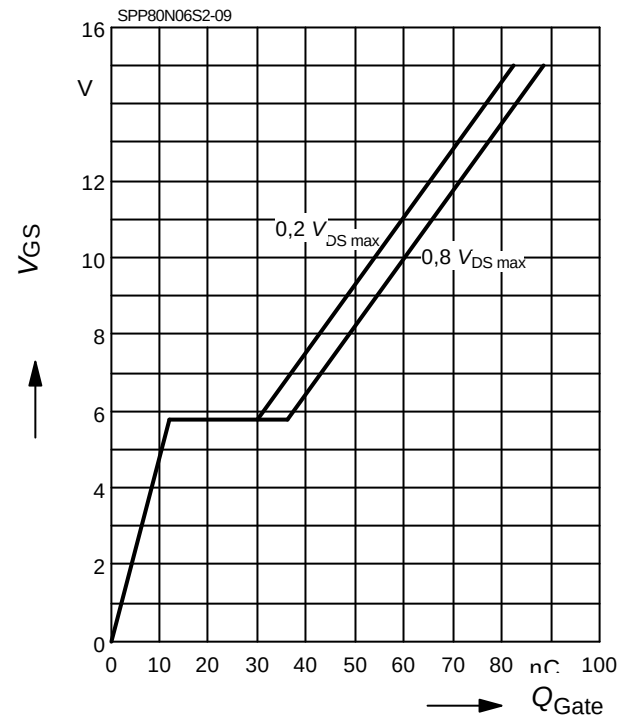
par.: $I_D = 80\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

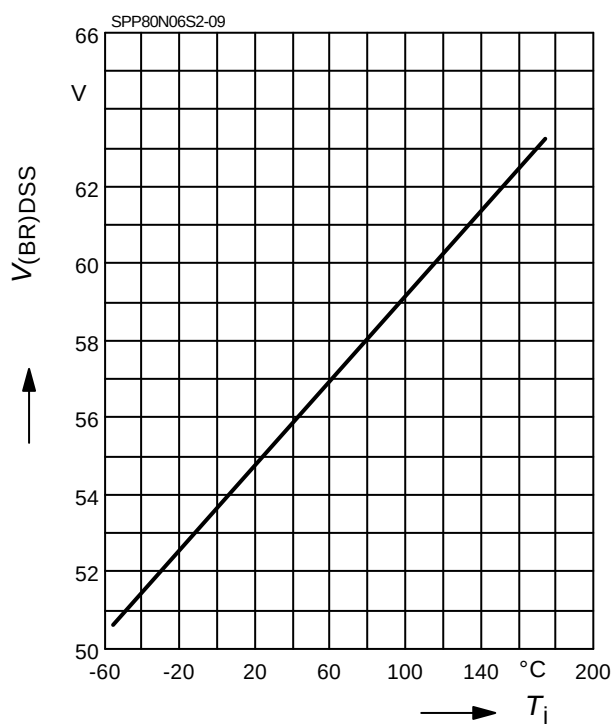
parameter: $I_D = 80\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter: $I_D = 10\text{ mA}$



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Further information

Please notice that the part number is **BSPP80N06S2-09** and **BSPB80N06S2-09**, for simplicity the device is referred to by the term **SPP80N06S2-09** and **SPB80N06S2-09** throughout this documentation.